$$- \overset{\mathbf{0.4}^{\mathbf{a_{2.1}}}}{\longmapsto} -$$

MOSFET ELECTRICAL CHARACTERISTICS Ta=25 ℃ unless otherwise specified

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V, V_{GS}=0V			-1	μA
		V_{DS}=-16V, V_{GS}=0V ,T_J=55℃			-5	
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}=±8V			±100	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.3	-0.55	-1	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-3A		81	97	mΩ
		V_{GS}=-4.5V, I_D=-3A T_J=125℃		111	135	
		V_{GS}=-2.5V, I_D=-2.6A		108	130	
		V_{GS}=-1.8V, I_D=-1A		146	190	
On state drain current	$I_{D(ON)}$	V_{GS}=-4.5V, V_{DS}=-5V	-15			A
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-3A	4	7		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-10V, f=1MHz		540		pF
Output Capacitance	C_{oss}			72		pF
Reverse Transfer Capacitance	C_{rss}			49		pF
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		12		Ω
Total Gate Charge	Q_g	V_{GS}=-4.5V, V_{DS}=- =-10V, I_D=-3A		6.1		nC
Gate Source Charge	Q_{gs}			0.6		nC
Gate Drain Charge	Q_{gd}			1.6		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS}=-4.5V, V_{DS}=-10V, R_L3.3Ω ,R_{GEN}=3Ω		10		ns
Turn-On Rise Time	t_r			12		ns
Turn-0ff DelayTime	$t_{D(off)}$			44		ns
Turn-Off Fall Time	t_f			22		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F=-3A, dI/dt=100A/μs		21		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=-3A, dI/dt=100A/μs		7.5		nC
Maximum Body-Diode Continuous Current	I_S				-2	A
Diode Forward Voltage	V_{SD}	I_S=-1A,V_{GS}=0V		-0.78	-1	V